

DECLARATION OF JOINT INVENTORS FOR PATENT APPLICATION

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled "Chemical Vapor Deposition Methods of Forming Barium Strontium Titanate Comprising Dielectric Layers, Including Such Layers Having a Varied Concentration of Titanium, Barium and Strontium Within the Layer", the specification of which is attached hereto.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to be material to patentability as defined in Title 37, Code of Federal Regulations § 1.56.

PRIOR FOREIGN APPLICATIONS:

I hereby state that no applications for foreign patents or inventor's certificates have been filed prior to the date of execution of this declaration.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States

Code and that such willful false statement may jeopardize the validity of the application or any patent issued therefrom.

* * * * *

Full name of inventor: **Cem Basceri**

Inventor's Signature: Cem Basceri

Date: 7-5-01

Residence: **Boise, Idaho**

Citizenship: **Turkey**

Post Office Address: **314 East Iowa Drive, Boise, Idaho 83706**

* * * * *

Full name of inventor: **Nancy Alzola**

Inventor's Signature: Nancy Alzola

Date: 7-5-01

Residence: **Boise, Idaho**

Citizenship: **U.S.A.**

Post Office Address: **10648 Hinsdale, Boise, ID 83713**

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. Unknown
 Filing Date Filed Herewith
 Inventor Cem Basceri et al.
 Assignee Micron Technology, Inc.
 Group Art Unit Unknown
 Examiner Unknown
 Attorney's Docket No. MI22-1657
 Title: Chemical Vapor Deposition Methods of Forming Barium Strontium
 Titanate Comprising Dielectric Layers, Including Such Layers Having a
 Varied Concentration of Titanium, Barium and Strontium Within the Layer

POWER OF ATTORNEY BY ASSIGNEE AND
CERTIFICATE BY ASSIGNEE UNDER 37 CFR § 3.73(b)

To: Assistant Commissioner for Patents
 Washington, D.C. 20231

Sir:

MICRON TECHNOLOGY, INC., the Assignee of the entire right, title and
 interest in the above-identified patent application by assignment attached
 hereto, hereby appoints the attorneys and agents of the firm of WELLS, ST.
 JOHN, ROBERTS, GREGORY & MATKIN P.S., listed as follows:

David P. Roberts	Reg. No. 23,032
Randy A. Gregory	Reg. No. 30,386
Mark S. Matkin	Reg. No. 32,268
James L. Price	Reg. No. 27,376
Deepak Malhotra	Reg. No. 33,560
Mark W. Hendricksen	Reg. No. 32,356
David G. Latwesen	Reg. No. 38,533
George G. Grigel	Reg. No. 31,166
Keith D. Grzelak	Reg. No. 37,144
James D. Shaurette	Reg. No. 39,833
Frederick M. Fliegel	Reg. No. 36,138
Donald Brent Kenady	Reg. No. 40,045
James E. Lake	Reg. No. 44,854

Bernard Berman
Jennifer J. Tayler, Ph.D.

Reg. No. 37,279
Reg. No. P 48,711

and also attorney Michael L. Lynch (Reg. No. 30,871) of Micron Technology, Inc., as its attorneys with full power of substitution to prosecute this application and transact all business in the Patent and Trademark Office connected therewith.

The Assignee certifies that the above-identified Assignment has been reviewed and to the best of Assignee's knowledge and belief, title is in the Assignee, and a copy of the Assignment is submitted herewith.

Please direct all correspondence regarding this application to:

Customer No. 021567
Wells, St. John, Roberts, Gregory & Matkin P.S.
Attn: Mark S. Matkin
601 West First Avenue, Suite 1300
Spokane, WA 99201-3828

Telephone: (509) 624-4276
Facsimile: (509) 838-3424

MICRON TECHNOLOGY, INC.

Dated: 7-9-2001

By: 

Name: Michael L. Lynch, Esq.
Title: Chief Patent Counsel

Attachment: Copy of Assignment; Copy of Board of Directors' Resolution

ASSIGNMENT

PARTIES TO THE ASSIGNMENT:

INVENTORS:

Cem Basceri
Nancy Alzola

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ASSIGNEE:

Micron Technology, Inc.
Corporation of the State of Delaware
8000 South Federal Way
Boise, Idaho 83716

BACKGROUND OF THIS ASSIGNMENT:

INVENTORS have conceived certain new and useful inventions disclosed in a United States patent application titled "Chemical Vapor Deposition Methods of Forming Barium Strontium Titanate Comprising Dielectric Layers, Including Such Layers Having a Varied Concentration of Titanium, Barium and Strontium Within the Layer".

MICRON TECHNOLOGY, INC. (hereinafter referred to as "ASSIGNEE") desires to acquire the entire right, title and interest in said inventions and with respect to any Letters Patent that may be granted with respect to the inventions in both the United States and in all foreign countries.

THE PARTIES AGREE AS FOLLOWS:

In consideration of good and valuable consideration, the receipt sufficiency and adequacy of which is hereby acknowledged, INVENTORS hereby sell, assign and transfer to ASSIGNEE the entire right, title and

COPY

interest in the above-identified application executed currently with this assignment and to any reissues, renewals, divisions or continuations thereof, and hereby authorizes the Commissioner of Patents and Trademarks to issue such Letters Patent to ASSIGNEE for the sole use of ASSIGNEE, its successors or assigns.

INVENTORS further agree to execute, at the request and expense of ASSIGNEE such other formal documents as may be required to fully convey the interest transferred herein and will similarly execute any application papers required for the filing of any division, continuation, renewal or reissue of the patent application or resulting Letters Patent; and will generally do everything necessary or desirable to obtain and enforce proper protection for the inventions assigned hereby.

INVENTORS further assign to ASSIGNEE the whole right, title and interest in the inventions disclosed in the application throughout all countries foreign to the United States. ASSIGNEE is hereby authorized to apply for patents relating to the inventions in its own name in countries where such procedure is proper; to claim the benefit of the International Convention; to file and prosecute International Applications relating to the inventions under the Patent Cooperation Treaty; and to file and prosecute applications relating to the inventions under the European Patent Convention. INVENTORS agree to execute applications relating to the inventions in those countries and under those conventions where it is necessary that the same be executed by the

inventor, and to execute assignments of such applications and the resulting Letters Patent to ASSIGNEE as well as all other necessary papers in relation to such applications and Letters Patent.

INVENTORS further warrant and covenant that no assignment, grant, mortgage, license or other agreement affecting the rights and property herein conveyed has been or will be made to others by the undersigned, and that the full rights to convey the same as herein expressed is possessed by the undersigned.

To be binding on the heirs, assigns, representatives and successors of the undersigned and extend to the successors, assigns and nominees of the Assignees.

Dated: 7/5/01

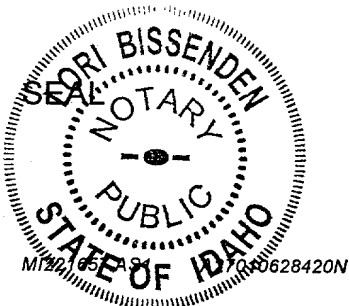
Signature: Cem Basceri
Cem Basceri

State of Idaho

County of Ada

)
) ss.
)

BEFORE ME, this 5th day of July, 2001 personally appeared the above-named inventor, known to me to be the person who is described in and who executed the foregoing assignment instrument and acknowledged to me that he executed the same of his own free will for the purpose therein expressed.



Seri Bissenden
Notary or Consular Officer
My Commission Expires: 6/12/2004

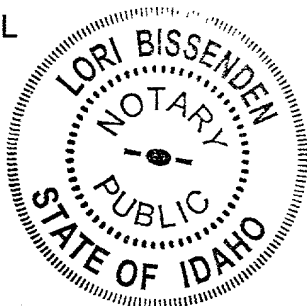
Dated: 7/5/01

Signature: Nancy Alzola
Nancy Alzola

State of Idaho)
County of Ada) ss.
)

BEFORE ME, this 5th day of July, 2001 personally appeared the above-named inventor, known to me to be the person who is described in and who executed the foregoing assignment instrument and acknowledged to me that she executed the same of her own free will for the purpose therein expressed.

SEAL



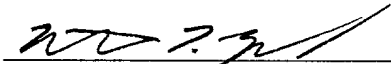
Lori Bissenden
Notary or Consular Officer
My Commission Expires: 6/12/2004

**MICRON TECHNOLOGY, INC.
CERTIFIED COPY OF RESOLUTIONS**

I, Jan R. Reimer, the Assistant Secretary of Micron Technology, Inc. do hereby certify, that the resolutions attached hereto represent a complete, true and correct copy of the resolutions duly adopted by the Board of Directors of Micron Technology, Inc., a corporation duly organized and existing under the laws of the State of Delaware, at a meeting duly held on March 25, 1996, a quorum being present, and have been entered into the minutes of said meeting; that I am the keeper of the corporate seal and of the minutes and records of this Corporation; and that the said resolutions have not been rescinded or modified.

The resolutions attached hereto are in conformity with the Articles of Incorporation and Bylaws of the Corporation and are now in full force and effect.

I further certify that the person whose name and signature is set out below is the person authorized to act for said corporation in transactions with and pursuant to the foregoing resolutions, and that such person is now duly qualified and acting in his respective capacity:

NAME AND TITLE	SIGNATURE
Michael L. Lynch, Assistant General Counsel for Intellectual Property	

IN WITNESS WHEREOF, I have hereunto subscribed my name and affixed the seal of the said corporation, this 6th day of May, 1996.


Jan R. Reimer, Assistant Secretary

(SEAL)

Country	Year	Population (millions)	Urban population (millions)	Urban population (%)	Population density (per sq km)	Urban population density (per sq km)	Population growth rate (%)	Urban population growth rate (%)	Population growth rate (%)	Urban population growth rate (%)	Population growth rate (%)	Urban population growth rate (%)
Algeria	1980	12.1	5.1	41.7	10.1	10.1	1.8	2.1	1.8	2.1	1.8	2.1
Algeria	1985	13.1	5.6	42.7	10.6	10.6	2.1	2.4	2.1	2.4	2.1	2.4
Algeria	1990	14.1	6.1	43.3	11.1	11.1	2.4	2.7	2.4	2.7	2.4	2.7
Algeria	1995	15.1	6.6	43.7	11.6	11.6	2.7	3.0	2.7	3.0	2.7	3.0
Algeria	2000	16.1	7.1	44.1	12.1	12.1	3.0	3.3	3.0	3.3	3.0	3.3
Algeria	2005	17.1	7.6	44.5	12.6	12.6	3.3	3.6	3.3	3.6	3.3	3.6
Algeria	2010	18.1	8.1	44.8	13.1	13.1	3.6	3.9	3.6	3.9	3.6	3.9
Algeria	2015	19.1	8.6	45.0	13.6	13.6	3.9	4.2	3.9	4.2	3.9	4.2
Algeria	2020	20.1	9.1	45.3	14.1	14.1	4.2	4.5	4.2	4.5	4.2	4.5
Algeria	2025	21.1	9.6	45.5	14.6	14.6	4.5	4.8	4.5	4.8	4.5	4.8
Algeria	2030	22.1	10.1	45.7	15.1	15.1	4.8	5.1	4.8	5.1	4.8	5.1
Algeria	2035	23.1	10.6	46.0	15.6	15.6	5.1	5.4	5.1	5.4	5.1	5.4
Algeria	2040	24.1	11.1	46.1	16.1	16.1	5.4	5.7	5.4	5.7	5.4	5.7
Algeria	2045	25.1	11.6	46.2	16.6	16.6	5.7	6.0	5.7	6.0	5.7	6.0
Algeria	2050	26.1	12.1	46.3	17.1	17.1	6.0	6.3	6.0	6.3	6.0	6.3
Algeria	2055	27.1	12.6	46.5	17.6	17.6	6.3	6.6	6.3	6.6	6.3	6.6
Algeria	2060	28.1	13.1	46.6	18.1	18.1	6.6	6.9	6.6	6.9	6.6	6.9
Algeria	2065	29.1	13.6	46.7	18.6	18.6	6.9	7.2	6.9	7.2	6.9	7.2
Algeria	2070	30.1	14.1	46.8	19.1	19.1	7.2	7.5	7.2	7.5	7.2	7.5
Algeria	2075	31.1	14.6	46.9	19.6	19.6	7.5	7.8	7.5	7.8	7.5	7.8
Algeria	2080	32.1	15.1	47.0	20.1	20.1	7.8	8.1	7.8	8.1	7.8	8.1
Algeria	2085	33.1	15.6	47.1	20.6	20.6	8.1	8.4	8.1	8.4	8.1	8.4
Algeria	2090	34.1	16.1	47.2	21.1	21.1	8.4	8.7	8.4	8.7	8.4	8.7
Algeria	2095	35.1	16.6	47.3	21.6	21.6	8.7	9.0	8.7	9.0	8.7	9.0
Algeria	2100	36.1	17.1	47.4	22.1	22.1	9.0	9.3	9.0	9.3	9.0	9.3
Algeria	2105	37.1	17.6	47.5	22.6	22.6	9.3	9.6	9.3	9.6	9.3	9.6
Algeria	2110	38.1	18.1	47.5	23.1	23.1	9.6	9.9	9.6	9.9	9.6	9.9
Algeria	2115	39.1	18.6	47.6	23.6	23.6	9.9	10.2	9.9	10.2	9.9	10.2
Algeria	2120	40.1	19.1	47.6	24.1	24.1	10.2	10.5	10.2	10.5	10.2	10.5
Algeria	2125	41.1	19.6	47.7	24.6	24.6	10.5	10.8	10.5	10.8	10.5	10.8
Algeria	2130	42.1	20									

Country	Year	Population (millions)	Urban population (millions)	Urban population (%)	Population density (per sq km)	Urban population density (per sq km)	Population growth rate (%)	Urban population growth rate (%)	Population growth rate (%)	Urban population growth rate (%)	Population growth rate (%)	Urban population growth rate (%)
Algeria	1980	12.1	5.1	41.7	10.1	10.1	1.8	2.1	1.8	2.1	1.8	2.1
Algeria	1985	13.1	5.6	42.7	10.6	10.6	2.1	2.4	2.1	2.4	2.1	2.4
Algeria	1990	14.1	6.1	43.3	11.1	11.1	2.4	2.7	2.4	2.7	2.4	2.7
Algeria	1995	15.1	6.6	43.7	11.6	11.6	2.7	3.0	2.7	3.0	2.7	3.0
Algeria	2000	16.1	7.1	44.1	12.1	12.1	3.0	3.3	3.0	3.3	3.0	3.3
Algeria	2005	17.1	7.6	44.5	12.6	12.6	3.3	3.6	3.3	3.6	3.3	3.6
Algeria	2010	18.1	8.1	44.8	13.1	13.1	3.6	3.9	3.6	3.9	3.6	3.9
Algeria	2015	19.1	8.6	45.0	13.6	13.6	3.9	4.2	3.9	4.2	3.9	4.2
Algeria	2020	20.1	9.1	45.3	14.1	14.1	4.2	4.5	4.2	4.5	4.2	4.5
Algeria	2025	21.1	9.6	45.5	14.6	14.6	4.5	4.8	4.5	4.8	4.5	4.8
Algeria	2030	22.1	10.1	45.7	15.1	15.1	4.8	5.1	4.8	5.1	4.8	5.1
Algeria	2035	23.1	10.6	46.0	15.6	15.6	5.1	5.4	5.1	5.4	5.1	5.4
Algeria	2040	24.1	11.1	46.1	16.1	16.1	5.4	5.7	5.4	5.7	5.4	5.7
Algeria	2045	25.1	11.6	46.2	16.6	16.6	5.7	6.0	5.7	6.0	5.7	6.0
Algeria	2050	26.1	12.1	46.3	17.1	17.1	6.0	6.3	6.0	6.3	6.0	6.3
Algeria	2055	27.1	12.6	46.5	17.6	17.6	6.3	6.6	6.3	6.6	6.3	6.6
Algeria	2060	28.1	13.1	46.6	18.1	18.1	6.6	6.9	6.6	6.9	6.6	6.9
Algeria	2065	29.1	13.6	46.7	18.6	18.6	6.9	7.2	6.9	7.2	6.9	7.2
Algeria	2070	30.1	14.1	46.8	19.1	19.1	7.2	7.5	7.2	7.5	7.2	7.5
Algeria	2075	31.1	14.6	46.9	19.6	19.6	7.5	7.8	7.5	7.8	7.5	7.8
Algeria	2080	32.1	15.1	47.0	20.1	20.1	7.8	8.1	7.8	8.1	7.8	8.1
Algeria	2085	33.1	15.6	47.1	20.6	20.6	8.1	8.4	8.1	8.4	8.1	8.4
Algeria	2090	34.1	16.1	47.2	21.1	21.1	8.4	8.7	8.4	8.7	8.4	8.7
Algeria	2095	35.1	16.6	47.3	21.6	21.6	8.7	9.0	8.7	9.0	8.7	9.0
Algeria	2100	36.1	17.1	47.4	22.1	22.1	9.0	9.3	9.0	9.3	9.0	9.3
Algeria	2105	37.1	17.6	47.5	22.6	22.6	9.3	9.6	9.3	9.6	9.3	9.6
Algeria	2110	38.1	18.1	47.5	23.1	23.1	9.6	9.9	9.6	9.9	9.6	9.9
Algeria	2115	39.1	18.6	47.6	23.6	23.6	9.9	10.2	9.9	10.2	9.9	10.2
Algeria	2120	40.1	19.1	47.6	24.1	24.1	10.2	10.5	10.2	10.5	10.2	10.5
Algeria	2125	41.1	19.6	47.7	24.6	24.6	10.5	10.8	10.5	10.8	10.5	10.8
Algeria	2130	42.1	20									

Country	Year	Population (millions)	Urban population (millions)	Urban population (%)	Population density (per sq km)	Urban population density (per sq km)	Population growth rate (%)	Urban population growth rate (%)	Population growth rate (%)	Urban population growth rate (%)	Population growth rate (%)	Urban population growth rate (%)
Algeria	1980	12.1	4.1	33.9	10.1	24.9	1.8	2.1	1.8	2.1	1.8	2.1
Algeria	1985	13.1	4.6	35.1	11.1	26.1	2.1	2.4	2.1	2.4	2.1	2.4
Algeria	1990	14.1	5.1	36.2	12.1	28.1	2.4	2.7	2.4	2.7	2.4	2.7
Algeria	1995	15.1	5.6	37.1	13.1	30.1	2.7	3.0	2.7	3.0	2.7	3.0
Algeria	2000	16.1	6.1	37.9	14.1	32.1	3.0	3.3	3.0	3.3	3.0	3.3
Algeria	2005	17.1	6.6	38.6	15.1	34.1	3.3	3.6	3.3	3.6	3.3	3.6
Algeria	2010	18.1	7.1	39.2	16.1	36.1	3.6	3.9	3.6	3.9	3.6	3.9
Algeria	2015	19.1	7.6	39.8	17.1	38.1	3.9	4.2	3.9	4.2	3.9	4.2
Algeria	2020	20.1	8.1	40.3	18.1	40.1	4.2	4.5	4.2	4.5	4.2	4.5
Algeria	2025	21.1	8.6	40.8	19.1	42.1	4.5	4.8	4.5	4.8	4.5	4.8
Algeria	2030	22.1	9.1	41.2	20.1	44.1	4.8	5.1	4.8	5.1	4.8	5.1
Algeria	2035	23.1	9.6	41.6	21.1	46.1	5.1	5.4	5.1	5.4	5.1	5.4
Algeria	2040	24.1	10.1	42.0	22.1	48.1	5.4	5.7	5.4	5.7	5.4	5.7
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Algeria	2060	28.1	12.1	43.3	26.1	56.1	6.6	6.9	6.6	6.9	6.6	6.9
Algeria	2065	29.1	12.6	43.6	27.1	58.1	6.9	7.2	6.9	7.2	6.9	7.2
Algeria	2070	30.1	13.1	43.9	28.1	60.1	7.2	7.5	7.2	7.5	7.2	7.5
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Algeria	2085	33.1	14.6	44.8	31.1	66.1	8.1	8.4	8.1	8.4	8.1	8.4
Algeria	2090	34.1	15.1	45.1	32.1	68.1	8.4	8.7	8.4	8.7	8.4	8.7
Algeria	2095	35.1	15.6	45.4	33.1	70.1	8.7	9.0	8.7	9.0	8.7	9.0
Algeria	2100	36.1	16.1	45.7	34.1	72.1	9.0	9.3	9.0	9.3	9.0	9.3
Algeria	2105	37.1	16.6	46.0	35.1	74.1	9.3	9.6	9.3	9.6	9.3	9.6
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Algeria	2125	41.1	18.6	47.2	39.1	82.1	10.5	10.8	10.5	10.8	10.5	10.8
Algeria	2130	42.1	19.1									